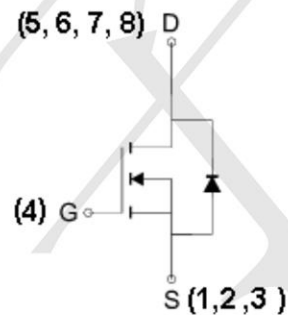
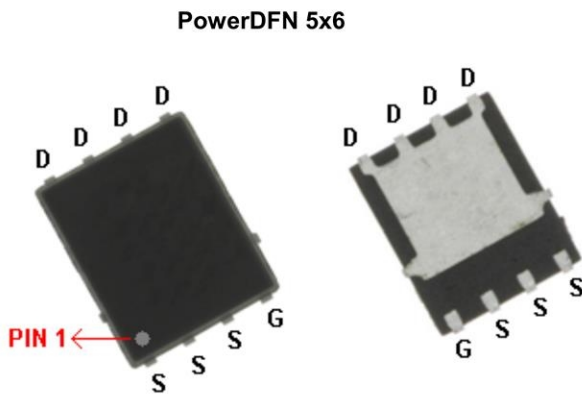


Product Summary

- ◆ $V_{DS} = 30V$ $I_D = 150A$
- $R_{DS(ON)} \leq 2.5m\Omega @ V_{GS} = 10V$
- $R_{DS(ON)} \leq 3.3m\Omega @ V_{GS} = 4.5V$

Application

- ◆ Load/Power switch
- ◆ Interfacing, logic switching
- ◆ Battery management for ultra portable electronics



N-Channel MOSFET

Marking:150N03

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise specified)

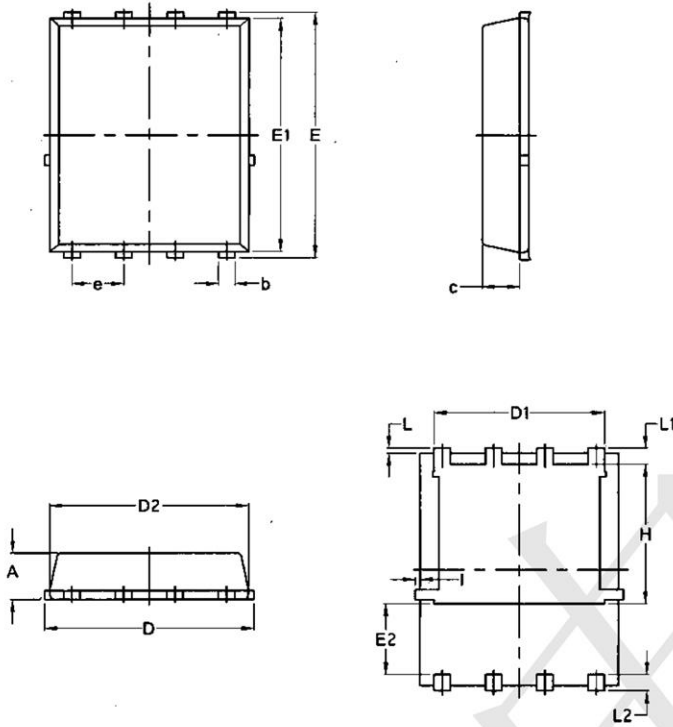
| Parameter | Symbol | Maximum Ratings | Unit |
|---|-----------------|---------------------|------------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain | | $T_C = 25^\circ C$ | 150 |
| | | $T_C = 100^\circ C$ | 100 |
| Pulsed Drain Current | I_{DM} | 350 | A |
| Maximum Power Dissipation* | P_D | $T_A = 25^\circ C$ | 75 |
| | | $T_A = 100^\circ C$ | 30 |
| Operating Junction Temperature | T_J | -55 to 150 | $^\circ C$ |
| Thermal Resistance-Junction to Ambient* | $R_{\theta JA}$ | Steady State | 45 |
| Thermal Resistance-Junction to Case* | $R_{\theta JC}$ | | 3.3 |

Electrical Characteristics (T = 25°C unless otherwise specified)

| Symbol | Parameter | Limit | Min | Typ | Max | Unit |
|----------------------|---|--|-----|------|------|------|
| STATIC | | | | | | |
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250 μA | 30 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250 μA | 1.3 | | 3.0 | V |
| I _{GSS} | Gate Leakage Current | V _{DS} =0V, V _{GS} =±20V | | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =30V, V _{GS} =0V | | | 1 | μA |
| R _{DS(ON)} | Drain-Source On-State Resistance ^a | V _{GS} =10V, I _D =27A | | 1.9 | 2.5 | mΩ |
| | | V _{GS} =4.5V, I _D =20A | | 2.5 | 3.3 | |
| V _{SD} | Diode Forward Voltage | I _S =2.8A, V _{GS} =0V | | 0.75 | 1.1 | V |
| DYNAMIC | | | | | | |
| Q _g | Total Gate Charge | V _{DS} =15V, V _{GS} =4.5V, I _D =27A | | 58 | | nC |
| Q _{gs} | Gate-Source Charge | | | 23 | | |
| Q _{gd} | Gate-Drain Charge | | | 30 | | |
| C _{iss} | Input Capacitance | V _{DS} =15V, V _{GS} =0V, F=1MHz | | 5930 | | pF |
| C _{oss} | Output Capacitance | | | 660 | | |
| C _{rss} | Reverse Transfer Capacitance | | | 220 | | |
| R _g | Gate-Resistance | V _{DS} =0V, V _{GS} =0V, F=1MHz | | 0.85 | | Ω |
| t _{d(on)} | Turn-On Delay Time | V _{DD} =15V, R _L =15Ω I _D =1A, V _{GEN} =10V R _G =6Ω | | 36 | | Ns |
| t _r | Turn-On Rise Time | | | 23 | | |
| t _{d(off)} | Turn-Off Delay Time | | | 170 | | |
| t _f | Turn-Off Fall Time | | | 44 | | |



Package Outline Dimensions PDFN5*6-8L



| Symbol | Common | | | |
|--------|----------|--------|----------|--------|
| | mm | | Inch | |
| | Min | Max | Min | Max |
| A | 1.03 | 1.17 | 0.0406 | 0.0461 |
| b | 0.34 | 0.48 | 0.0134 | 0.0189 |
| c | 0.824 | 0.0970 | 0.0324 | 0.082 |
| D | 4.80 | 5.40 | 0.1890 | 0.2126 |
| D1 | 4.11 | 4.31 | 0.1618 | 0.1697 |
| D2 | 4.80 | 5.00 | 0.1890 | 0.1969 |
| E | 5.95 | 6.15 | 0.2343 | 0.2421 |
| E1 | 5.65 | 5.85 | 0.2224 | 0.2303 |
| E2 | 1.60 | / | 0.0630 | / |
| e | 1.27 BSC | | 0.05 BSC | |
| L | 0.05 | 0.25 | 0.0020 | 0.0098 |
| L1 | 0.38 | 0.50 | 0.0150 | 0.0197 |
| L2 | 0.38 | 0.50 | 0.0150 | 0.0197 |
| H | 3.30 | 3.50 | 0.1299 | 0.1378 |
| l | / | 0.18 | / | 0.0070 |